

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1203

AUDIO FREQUENCY AMPLIFIER APPLICATIONS

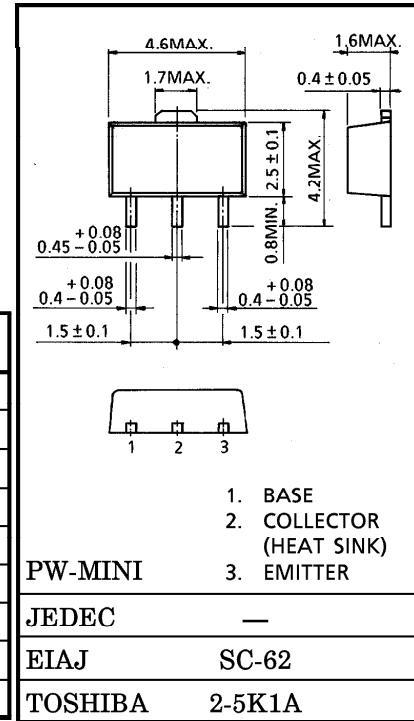
Unit in mm

- Suitable for Output Stage of 3 Watts Amplifier
- PC=1~2W (Mounted on Ceramic Substrate)
- Small Flat Package
- Complementary to 2SC2883

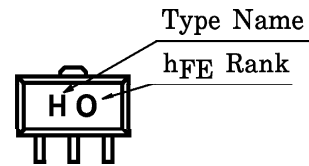
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-30	V
Collector-Emitter Voltage	V _{CEO}	-30	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-1.5	A
Base Current	I _B	-0.3	A
Collector Power Dissipation	P _C	500	mW
Collector Power Dissipation	P _C * [†]	1000	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

P_C* : Mounted on ceramic substrate (250mm²×0.8t)



Weight : 0.05g
Marking



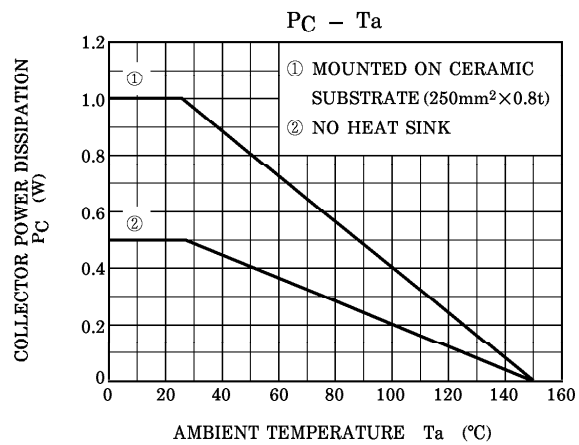
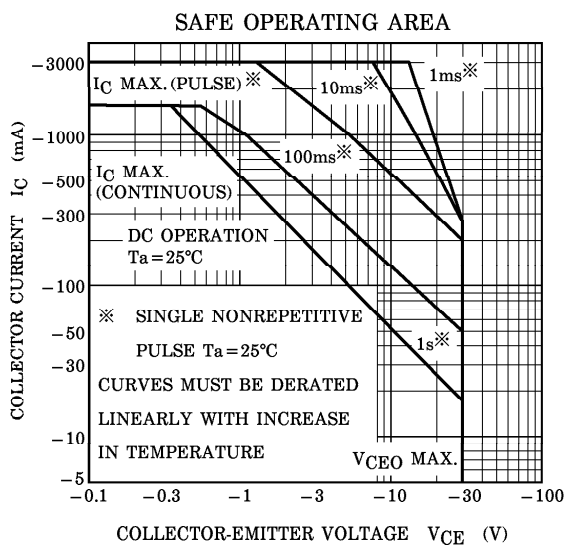
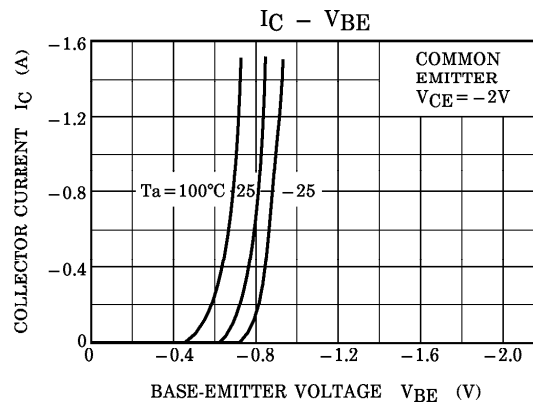
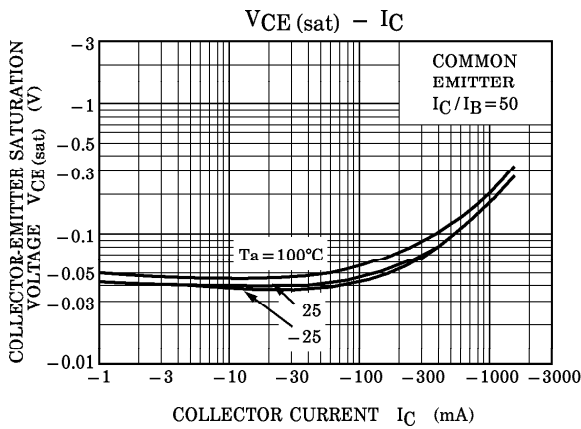
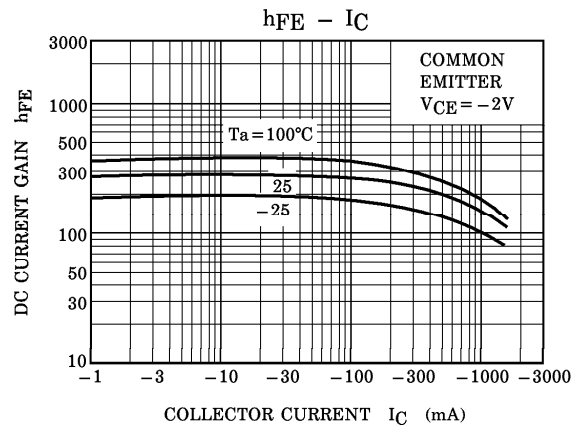
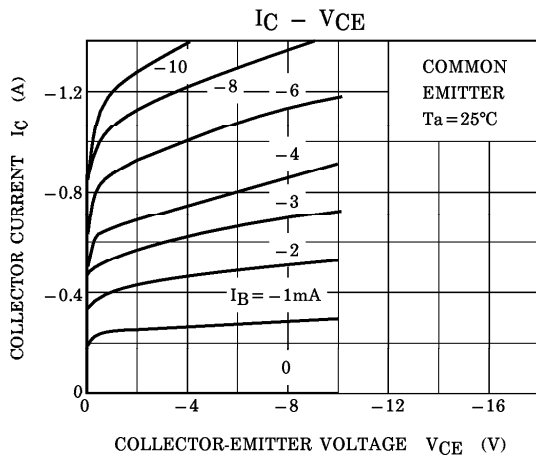
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} = -30V, I _E = 0	—	—	-0.1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} = -5V, I _C = 0	—	—	-0.1	μA
Collector-Emitter Breakdown Voltage	V (BR) CEO	I _C = -10mA, I _B = 0	-30	—	—	V
Emitter-Base Breakdown Voltage	V (BR) EBO	I _E = -1mA, I _C = 0	-5	—	—	V
DC Current Gain	h _{FE} (Note)	V _{CE} = -2V, I _C = -500mA	100	—	320	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C = -1.5A, I _B = -0.03A	—	—	-2.0	V
Base-Emitter Voltage	V _{BE}	V _{CE} = -2V, I _C = -500mA	—	—	-1.0	V
Transition Frequency	f _T	V _{CE} = -2V, I _C = -500mA	—	120	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz	—	—	50	pF

Note : h_{FE} Classification O : 100~200, Y : 160~320

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